Customer No.: 31,561
Application No.: 10/709,038
Docket No.: 09005-US-PA

AMENDMENTS

To the Specification

Please amend the paragraphs as follows:

[0040] Referring to **FIG. 3D**, a dielectric layer ~~317~~318 is formed over the first poly-Si layer **310** and the second opening **316**, wherein the dielectric layer ~~317~~318 can be formed by, for example, performing a conventional process such as either LPCVD, PECVD or sputtering, wherein the dielectric layer ~~317~~318 includes a recess **320** neighboring with the second opening **316**.

[0041] Referring to **FIG. 3E**, a second a-Si layer ~~318~~322 is formed over the dielectric layer ~~317~~318, wherein the second a-Si layer ~~318~~322 is formed by, for example, performing with a conventional deposition process such as a LPCVD, a PECVD, or a sputtering process. Thereafter, the resulting structure is subjected to a second laser annealing ~~322~~324 by performing, for example, an excimer laser annealing, to irradiate the second a-Si layer ~~318~~322. The energy density of the excimer laser is about 50 to 500 mJ/cm^2.

[0042] Finally, referring to **FIG. 3F**, a second poly-Si layer ~~324~~326 is formed transformed from a fused portion of the second a-Si layer ~~318~~322 crystal growing in a lateral direction ~~326~~328, wherein an unfused portion of the second a-Si layer ~~318~~322 neighboring with the recess **320** serves as a seed for crystallization.

[0048] Next, referring to **FIG. 4D**, a dielectric layer **~~417~~418** is formed over the first poly-Si layer **410** and the second opening **416**, wherein the dielectric layer **~~417~~418** can be formed by performing LPCVD, PECVD or sputtering, for example. A second hole **420** is formed as an air space in the dielectric layer **~~417~~418**, wherein the second hole **420** is neighboring with the second opening 416.

[0049] Furthermore, referring to **FIG. 4E**, a second a-Si layer **~~418~~422** is formed over the dielectric layer **~~417~~418**, wherein the second a-Si layer **~~418~~422** is formed by performing LPCVD, PECVD or sputtering, for example. Thereafter, the resulting structure is subjected to a second laser annealing **~~422~~424** by performing an excimer laser annealing for example, to irradiate and fuse the second a-Si layer **~~418~~422**. The energy density of the excimer laser is about 50 to 500 mJ/cm^2.

[0050] Finally, referring to **FIG. 4F**, a second poly-Si layer **~~424~~426** is transformed from the second a-Si layer **~~418~~422** through fusion and crystallization. When the second laser annealing **~~422~~424** is performed, a portion of the second a-Si layer **~~418~~422** over the second hole **420** is subjected to a higher temperature than other portion of the second a-Si player **~~418~~422** relative to the second hole **420** because the thermal conductivity is poor around the second hole **420**. A

lateral crystallization progress from a region with lowest temperature (not shown) along the direction ~~426~~428 is performed, wherein the lateral crystallization lasts longer around the second hole 420.